# SKHI 21A (R) ...



SEMIDRIVERTM

# Hybrid Dual MOSFET Driver

#### SKHI 21A (R)

Preliminary Data

## Features

- drives MOSFETs with V<sub>DS(on)</sub> < 10 V</li>
- is compatible to old SKHI 21
- CMOS compatible inputs
- Short circuit potection by V<sub>CE</sub> monitoring and switch off
- Drive interlock top / bottom
- Isolation by transformers
- Supply undervotage protection (13 V)
- Error latch / output

### **Typical Applications**

 Driver for MOSFET modules in bridge circuits in choppers, inverter drives, UPS and welding inverters

1) see fig. 6

2) At  $R_{CE}$  = 18 k $\Omega$ ,  $C_{CE}$  = 330 pF

Absolute Maximum Ratings						
Symbol	Conditions	Values	Units			
Vs	Supply voltage prim.	18	V			
V <sub>iH</sub>	Input signal volt. (High)	V <sub>S</sub> + 0,3	V			
lout <sub>PEAK</sub>	Output peak current	8	А			
lout <sub>AVmax</sub>	Output average current	40	mA			
f <sub>max</sub>	max. switching frequency	50	kHz			
V <sub>CE</sub>	Collector emitter voltage sense across the IGBT	1200	V			
dv/dt	Rate of rise and fall of voltage secondary to primary side	50	kV/μs			
V <sub>isollO</sub>	Isolation test voltage	2500	Vac			
100110	input - output (2 sec. AC)					
V <sub>isol12</sub>	Isolation test voltage	1500	V			
	output 1 - output 2 (2 sec. AC)					
R <sub>Gonmin</sub>	Minimum rating for R <sub>Gon</sub>	3	Ω			
R <sub>Goffmin</sub>	Minimum rating for R <sub>Goff</sub>	3	Ω			
Q <sub>out/pulse</sub>	Max. rating for output charge per pulse	4 <sup>1)</sup>	μC			
T <sub>op</sub>	Operating temperature	- 40 + 85	°C			
T <sub>stg</sub>	Storage temperature	- 40 + 85	°C			

Characte	ristics T	$\Gamma_a = 25 ^{\circ}\text{C}$ , unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
Vs	Supply voltage primary side	14,4	15	15,6	V	
I <sub>SO</sub>	Supply current primary side (no load)		80		mA	
	Supply current primary side (max.)			290	mA	
Vi	Input signal voltage on/off		15 / 0		V	
V <sub>iT+</sub>	Input threshold voltage (High)	10,9	11,7	12,5	V	
V <sub>iT-</sub>	Input threshold voltage (Low)	4,7	5,5	6,5	V	
R <sub>in</sub>	Input resistance		10		kΩ	
V <sub>G(on)</sub>	Turn on gate voltage output		+ 15		V	
V <sub>G(off)</sub>	Turn off gate voltage output		0		V	
R <sub>GE</sub>	Internal gate-emitter resistance		22		kΩ	
f <sub>ASIC</sub>	Asic system switching frequency		8		MHz	
t <sub>d(on)IO</sub>	Input-output turn-on propagation time	0,85	1	1,15	μs	
t <sub>d(off)IO</sub>	Input-output turn-off propagation time	0,85	1	1,15	μs	
t <sub>d(err)</sub>	Error input-output propagation time		0,6		μs	
t <sub>pERRRESET</sub>	Error reset time		9		μs	
t <sub>TD</sub>	Top-Bot Interlock Dead Time	3,3		4,3	μs	
V <sub>CEsat</sub>	Reference voltage for V <sub>CE</sub> -monitoring		5 <sup>2)</sup>	10	V	
C <sub>ps</sub>	Coupling capacitance primary secondary		12		pF	
MTBF	Mean Time Between Failure T <sub>a</sub> = 40°C		2,0		10 <sup>6</sup> h	
w	weight		45		g	

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.